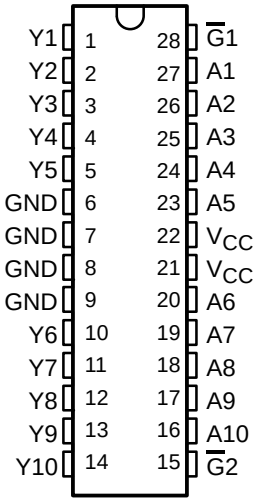
- **3-State Outputs Drive Bus Lines or Buffer Memory Address Registers**
- **Flow-Through Architecture to Optimize PCB Layout**
- **Center-Pin V_{CC} and GND Configurations to Minimize High-Speed Switching Noise**
- **EPIC™ (Enhanced-Performance Implanted CMOS) 1-μm Process**
- **500-mA Typical Latchup Immunity at 125°C**
- **Package Options Include Plastic "Small Outline" Packages and Standard Plastic 300-mil DIPs**

DW OR NT PACKAGE
(TOP VIEW)



description

This device contains ten buffers/bus drivers that provide a high-performance 10-bit bus interface for wide data paths or buses carrying parity.

The 3-state control gate is a 2-input NOR gate. If either $\overline{G}1$ or $\overline{G}2$ is high, all ten outputs are in the high-impedance state.

The 74AC11828 provides inverted data.

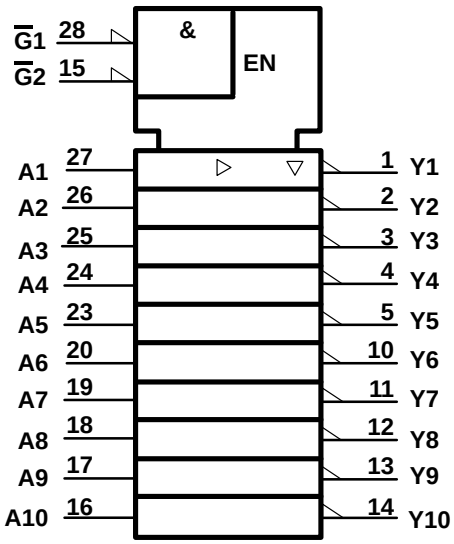
The 74AC11828 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

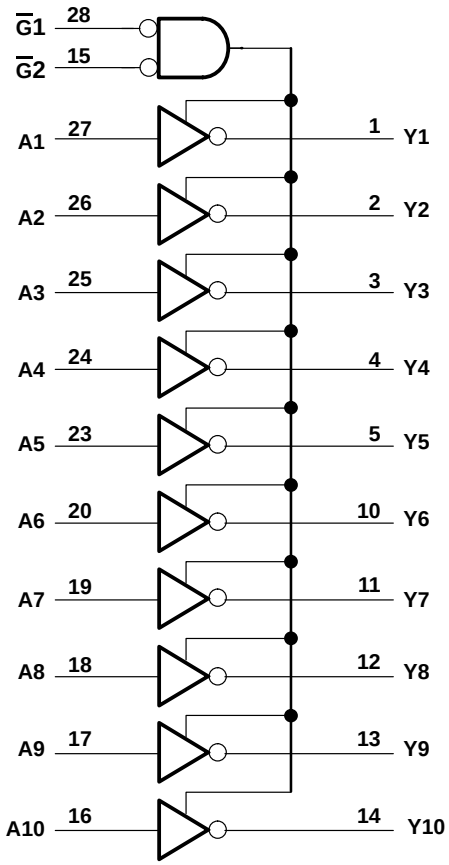
INPUTS			OUTPUT
$\overline{G}1$	$\overline{G}2$	A	Y
L	L	H	L
L	L	L	H
X	H	X	Z
H	X	X	Z

EPIC is a trademark of Texas Instruments Incorporated.

logic symbol †



logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . – 0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Note 1) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$ or $V_I > V_{CC}$) . . . . . ± 20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$) . . . . . ± 50 mA
Continuous output current, I_O ($V_O = 0$ to V_{CC}) . . . . . ± 50 mA
Continuous current through V_{CC} or GND pins . . . . . ± 250 mA
Storage temperature range . . . . . –65°C to 150°C

‡ Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

recommended operating conditions

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		3	5	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 3 V	2.1			V
		V_{CC} = 4.5 V	3.15			
		V_{CC} = 5.5 V	3.85			
V_{IL}	Low-level input voltage	V_{CC} = 3 V			0.9	V
		V_{CC} = 4.5 V			1.35	
		V_{CC} = 5.5 V			1.65	
V_I	Input voltage		0		V_{CC}	V
V_O	Output voltage		0		V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 3 V			–4	mA
		V_{CC} = 4.5 V			–24	
		V_{CC} = 5.5 V			–24	
I_{OL}	Low-level output current	V_{CC} = 3 V			12	mA
		V_{CC} = 4.5 V			24	
		V_{CC} = 5.5 V			24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0		10	ns/V
T_A	Operating free-air temperature		–40		85	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	T_A = 25°C			MIN	MAX	UNIT
			MIN	TYP	MAX			
V_{OH}	I_{OH} = –50 µA	3 V	2.9			2.9		V
		4.5 V	4.4			4.4		
		5.5 V	5.4			5.4		
	I_{OH} = –4 mA	3 V	2.58			2.48		
	I_{OH} = –24 mA	4.5 V	3.94			3.8		
		5.5 V	4.94			4.8		
	I_{OH} = –75 mA†	5.5 V				3.85		
V_{OL}	I_{OL} = 50 µA	3 V			0.1		0.1	V
		4.5 V			0.1		0.1	
		5.5 V			0.1		0.1	
	I_{OL} = 12 mA	3 V			0.36		0.44	
	I_{OL} = 24 mA	4.5 V			0.36		0.44	
		5.5 V			0.36		0.44	
	I_{OL} = 75 mA†	5.5 V					1.65	
I_{OZ}	V_O = V_{CC} or GND	5.5 V			±0.5		±5	µA
I_I	V_I = V_{CC} or GND	5.5 V			±0.1		±1	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	5.5 V			8		80	µA
C_i	V_I = V_{CC} or GND	5 V		4.5				pF
C_o	V_O = V_{CC} or GND	5 V		12				pF

† Not more than one output should be tested at a time, and the duration of the test should not exceed 10 ms.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T_A = 25°C			MIN	MAX	UNIT
			MIN	TYP	MAX			
t_{PLH}	A	Y	5.4	9.8	12.7	5.4	14.3	ns
t_{PHL}			7.2	10.4	13.2	7.2	14.5	
t_{PZH}	G1 or G2	Y	6.5	10.8	14.4	6.5	16.3	ns
t_{PZL}			9.5	15	19.2	9.5	21.8	
t_{PHZ}	G1 or G2	Y	5.3	8.2	11	5.3	11.9	ns
t_{PLZ}			5.1	7.9	10.5	5.1	11.2	

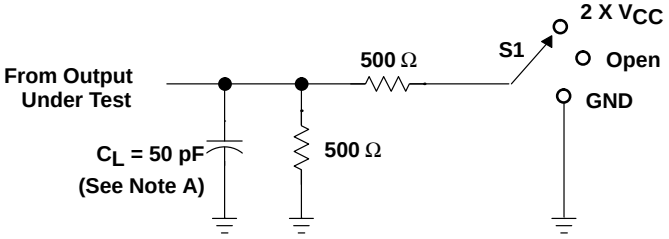
switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T_A = 25°C			MIN	MAX	UNIT
			MIN	TYP	MAX			
t_{PLH}	A	Y	2.4	5.2	7.9	2.4	9.5	ns
t_{PHL}			3.2	6.2	8.9	3.2	10.4	
t_{PZH}	G1 or G2	Y	3.1	6.4	8.8	3.1	10.7	ns
t_{PZL}			3.8	7.7	10.5	3.8	13.2	
t_{PHZ}	G1 or G2	Y	3.7	6.4	8.8	3.7	9.6	ns
t_{PLZ}			3.9	6.2	8.2	3.9	9.2	

operating characteristics, V_{CC} = 5 V, T_A = 25°C

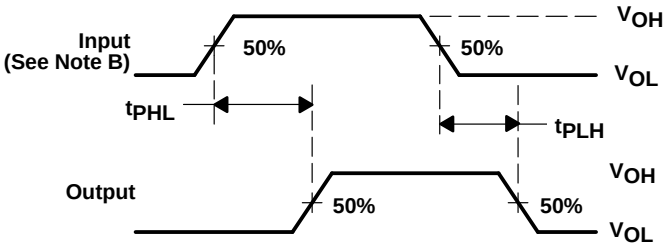
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd} Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 1 MHz	37	pF
	Outputs disabled		11	

PARAMETER MEASUREMENT INFORMATION

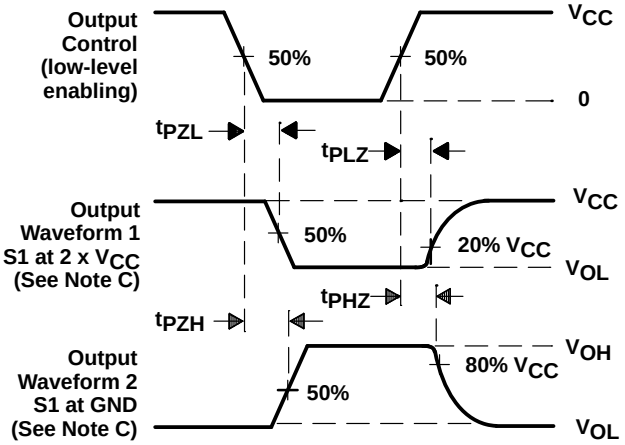


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	2 x V_{CC}
t_{PHZ}/t_{PZH}	GND

LOAD CIRCUIT FOR OUTPUTS



PROPAGATION DELAY TIMES



ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by the generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. LOAD CIRCUIT AND VOLTAGE WAVEFORMS

IMPORTANT NOTICE

Texas Instruments (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Certain applications using semiconductor products may involve potential risks of death, personal injury, or severe property or environmental damage ("Critical Applications").

TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS.

Inclusion of TI products in such applications is understood to be fully at the risk of the customer. Use of TI products in such applications requires the written approval of an appropriate TI officer. Questions concerning potential risk applications should be directed to TI through a local SC sales office.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.